

Title (en)
METHODS FOR SEPARATING MICROCIRCUIT DIES FROM WAFERS

Title (de)
VERFAHREN ZUR ABTRENNUNG VON MIKROSCHALTUNGBAUSTEINEN AUS EINEM HALBLEITERWAFER

Title (fr)
PROCEDES POUR SEPARER LES PUCES A MICROCIRCUITS DE TRANCHES DE SEMICONDUCTEURS

Publication
EP 1238423 A2 20020911 (EN)

Application
EP 00992379 A 20001130

Priority
• US 0042507 W 20001130
• US 45646699 A 19991208

Abstract (en)
[origin: WO0143169A2] Methods are provided for separating microcircuit dies from a wafer, which includes microcircuit dies containing componentry on a circuit side thereof and streets separating the dies from each other. A first wafer mount film is affixed to the circuit side of the wafer, and the dies are detached along the streets with the circuit side of the wafer fixed to the first wafer mount film, thereby forming a divided wafer. A second wafer mount film is fixed to the back side of the divided wafer, and the first wafer mount film is removed from the divided wafer so that the dies remain fixed to the second wafer mount film with their circuit sides exposed. The second wafer mount film preferably has greater adhesion to the divided wafer than the first wafer mount film when the first wafer mount film is removed from the divided wafer. The first wafer mount film may comprise a protective film having holes aligned with fragile components on the dies and a cover film that covers the holes. The protective film may be an ultraviolet-curable film that exhibits reduced adhesion to the divided wafer after exposure to ultraviolet radiation.

IPC 1-7
H01L 21/78; B81C 1/00

IPC 8 full level
H01L 21/301 (2006.01); **H01L 21/02** (2006.01); **H01L 21/68** (2006.01); **H01L 21/78** (2006.01); **H01L 23/544** (2006.01)

CPC (source: EP)
H01L 21/6836 (2013.01); **H01L 21/78** (2013.01); **H01L 23/544** (2013.01); **H01L 2221/68327** (2013.01); **H01L 2223/5442** (2013.01); **H01L 2223/54453** (2013.01); **H01L 2223/54466** (2013.01); **H01L 2924/0002** (2013.01); **H01L 2924/19041** (2013.01); **H01L 2924/30105** (2013.01)

Citation (search report)
See references of WO 0143169A2

Designated contracting state (EPC)
DE FR GB

DOCDB simple family (publication)
WO 0143169 A2 20010614; **WO 0143169 A3 20011213**; EP 1238423 A2 20020911; JP 2003516630 A 20030513

DOCDB simple family (application)
US 0042507 W 20001130; EP 00992379 A 20001130; JP 2001543761 A 20001130